

# Dual General Purpose Transistors

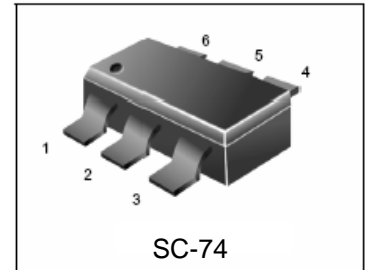
## PNP Duals

- We declare that the material of product compliance with RoHS requirements.

**LBC807-16DMT1G**  
**LBC807-25DMT1G**  
**LBC807-40DMT1G**

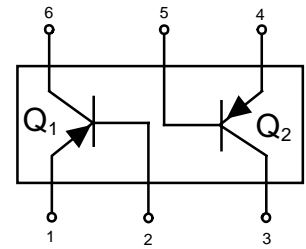
### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	45	V
Collector–Base Voltage	$V_{CBO}$	50	V
Emitter–Base Voltage	$V_{EBO}$	5.0	V
Collector Current — Continuous	$I_C$	500	mAdc



### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) $T_A = 25^\circ\text{C}$	$P_D$	370	mW
Derate above $25^\circ\text{C}$		3.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	333	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	$P_D$	600	mW
Derate above $25^\circ\text{C}$		4.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	208	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$



### DEVICE MARKING

LBC807–16DMT1G = 5A; LBC807–25DMT1G = 5B; LBC807–40DMT1G = 5C

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ( $I_C = -10\text{ mA}$ )	$V_{(BR)CEO}$	45	—	—	V
Collector–Emitter Breakdown Voltage ( $V_{EB} = 0, I_C = -10\ \mu\text{A}$ )	$V_{(BR)CES}$	50	—	—	V
Emitter–Base Breakdown Voltage ( $I_E = -1.0\ \mu\text{A}$ )	$V_{(BR)EBO}$	5.0	—	—	V
Collector Cutoff Current ( $V_{CB} = 20\text{ V}$ )	$I_{CBO}$	—	—	100	nA
( $V_{CB} = 20\text{ V}, T_A = 150^\circ\text{C}$ )		—	—	5.0	$\mu\text{A}$

1. FR–5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

**LBC807-16DMT1G LBC807-25DMT1G LBC807-40DMT1G**
**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
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**ON CHARACTERISTICS**

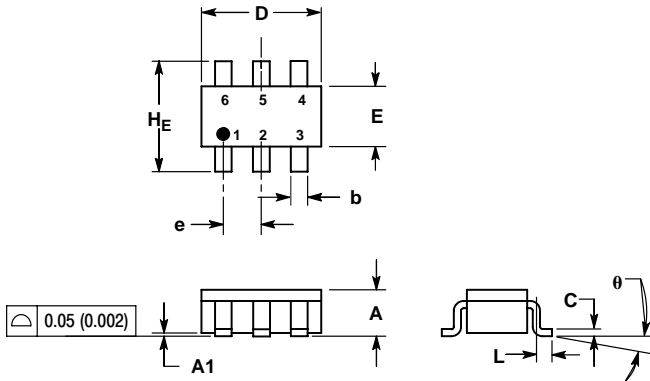
DC Current Gain ( $I_C = 100\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ )	$h_{FE}$	100	—	250	
	LBC807-16	160	—	400	
	LBC807-25	250	—	600	
	LBC807-40	40	—	—	
Collector-Emitter Saturation Voltage ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{CE(sat)}$	—	—	0.7	V
Base-Emitter On Voltage ( $I_C = 500\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ )	$V_{BE(on)}$	—	—	1.2	V

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain — Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 5.0\text{ V}_{dc}$ , $f = 100\text{ MHz}$ )	$f_T$	100	—	—	MHz
Output Capacitance ( $V_{CB} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	—	10	—	pF

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### SC-74



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
$\theta$	0°	-	10°	0°	-	10°

